

ABSTRACT

Disclosed in a method of forming a metal line in a semiconductor device. The method includes the steps of sequentially forming a first etch stop film, a second interlayer insulating film and a BARC film on a first interlayer
5 insulating film into which a metal line is buried, forming a photoresist pattern defining a trench in a given region of the BARC film, performing an etch process up to the second interlayer insulating film using the photoresist pattern as an etch mask to form a trench, removing the photoresist pattern and the BARC film by means of a first wet etch process, etching the first etch stop
10 film by means of a second wet etch process using the second interlayer insulating film as an etch mask, and cleaning the resulting entire surface by means of a third wet etch process. As such, by removing the photoresist pattern, the BARC film and the etch stop film through the wet etch process, it is possible to reduce the amount of polymer generated in the process for
15 forming the via hole and the metal line trench.